

1.1 Scope.

This specification covers the requirements for an accurately programmable gain instrumentation amplifier. The gain equation is $\frac{R_S}{R_G} \frac{V}{V}$.

1.2 Part Number.

The complete part number per Table 1 of this specification is as follows:

Device	Part Number
-1	AD521SD/883B

1.2.3 Case Outline.

See Appendix 1 of General Specification ADI-M-1000: package outline: D-14.

1.3 Absolute Maximum Ratings. ($T_A = +25^\circ\text{C}$ unless otherwise noted)

Supply Voltage	$\pm 18\text{ V}$
Internal Power Dissipation ¹	500 mW
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Operating Temperature Range	-55°C to $+125^\circ\text{C}$
Lead Temperature Range (Soldering 10 sec)	$+300^\circ\text{C}$

NOTE

¹Maximum package power dissipation vs. ambient temperature.

Package Type	MAXIMUM AMBIENT Temperature for Rating	DERATE ABOVE MAXIMUM Ambient Temperature
D-14	$+80^\circ\text{C}$	7.1 mW/ $^\circ\text{C}$

1.5 Thermal Characteristics.

Thermal Resistance $\theta_{JC} = 22^\circ\text{C}/\text{W}$
 $\theta_{JA} = 95^\circ\text{C}/\text{W}$

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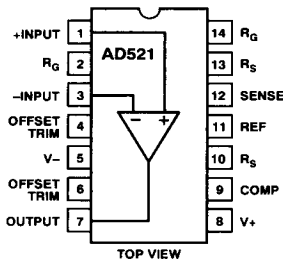
Table 1.

Test	Symbol	Device	Sub Group 1	Sub Group 2, 3	Test Conditions ¹	Unit
Input Offset Voltage	V_{OSI}	-1	1.5			$\pm$ mV max
Input Offset Voltage Drift	TCV_{OSI}	-1		5		$\pm$ μ V/ $^{\circ}$ C max
Output Offset Voltage	V_{OSO}	-1	200			$\pm$ mV max
Output Offset Voltage Drift	TCV_{OSO}	-1		150		$\pm$ μ V/ $^{\circ}$ C max
Input Offset Current	I_{OS}	-1	10			$\pm$ nA max
Input Offset Current Drift	TCI_{OS}	-1		125		$\pm$ pA/ $^{\circ}$ C max
Input Bias Current	I_B	-1	40			$\pm$ nA max
Input Bias Current Drift	TCI_B	-1		500		$\pm$ pA/ $^{\circ}$ C max
Gain Nonlinearity	GN	-1	0.2		$1 < G < 1000$; $V_{OUT} = \pm 10$ V	$\pm$ % max
Common-Mode Rejection Ratio	$CMRR_1$	-1	74		$G = 1$; dc	dB min
Common-Mode Rejection Ratio	$CMRR_{1000}$	-1	110		$G = 1000$; dc	dB min
Output Voltage Swing	V_{OUT}	-1	10		$R_L = 1$ k Ω	$\pm$ V min

NOTE

¹ $V_S = \pm 15$ V, $R_L = 2$ k Ω , unless otherwise noted.

3.2.1 Functional Block Diagram and Terminal Assignments.



3.2.4 Microcircuit Technology Group.

This microcircuit is covered by technology group (49).

4.2.1 Life Test/Burn-In Circuit.

Steady state life test is per MIL-STD-883 Method 1005.

Burn-in is per MIL-STD-883 Method 1015 test condition (B).

